# **RT5N227C**

Transistor With Resistor For Switching Application Silicon NPN Epitaxial Type

### **DESCRIPTION**

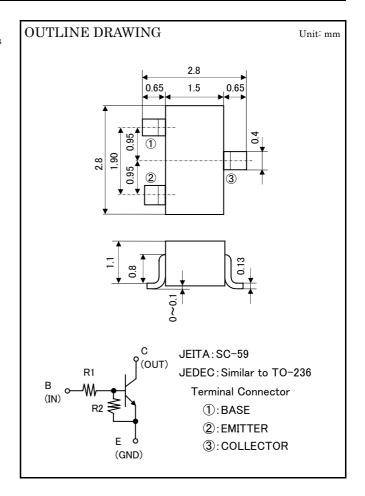
RT5N227C is a one chip transistor with built-in bias resistor, PNP type is RT5P227C.

### **FEATURE**

Built-in bias resistor ( $R_1$ =0.22k $\Omega$ ,  $R_2$ =4.7k $\Omega$ ) High collector current (Ic=0.5A) Mini package for easy mounting

### **APPLICATION**

Inverted circuit, Switching circuit, Interface circuit, Driver circuit



# MAXIMUM RATING (Ta=25°C)

| SYMBOL                    | PARAMETER                      | RATING   | UNIT |  |
|---------------------------|--------------------------------|----------|------|--|
| $V_{\mathrm{CBO}}$        | Collector to Base voltage      | 50       | V    |  |
| $V_{\mathrm{EBO}}$        | Emitter to Base voltage        | 5        | V    |  |
| $V_{\rm IN}$              | Input voltage                  | 5        | V    |  |
| $V_{\rm CEO}$             | Collector to Emitter voltage   | 50       | V    |  |
| $\mathbf{I}_{\mathrm{C}}$ | Collector current              | 500      | mA   |  |
| Pc                        | Collector dissipation(Ta=25°C) | 200      | mW   |  |
| $T_{\rm j}$               | Junction temperature           | +150     | °C   |  |
| $T_{ m stg}$              | Storage temperature            | -55~+150 | င    |  |

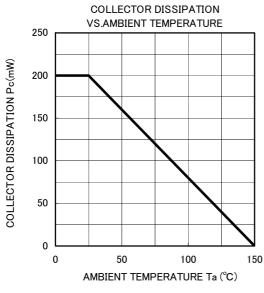


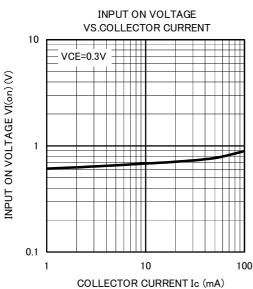
# ELECTRICAL CHARACTERISTICS (Ta=25°C)

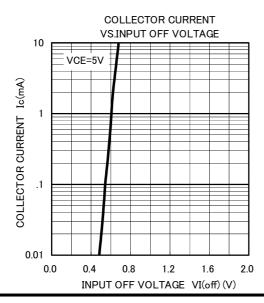
| SYMBOL                          | PARAMETER                 | TEST CONDITION                             | LIMIT |      |       | TINIIM |
|---------------------------------|---------------------------|--|-------|------|-------|--------|
|                                 |                           |  | MIN   | TYP  | MAX   | UNIT   |
| $V_{I(on)}$                     | Input on voltage          | $V_{CE}$ =0.3V, $I_{C}$ =30mA              | _     | _    | 2     | V      |
| $V_{\rm I(off)}$                | Input off voltage         | V <sub>CE</sub> =5V, I <sub>C</sub> =100μA | 0.5   | _    | _     | V      |
| $V_{\mathrm{CE}(\mathrm{sat})}$ | C to E saturation voltage | $I_C=50$ mA, $I_B=2.5$ mA                  | _     | 0.1  | 0.3   | V      |
| $\mathbf{I}_{\mathrm{BE}}$      | B to E current            | $V_{BE}=5V$                                | _     | _    | 45    | mA     |
| $I_{CES}$                       | Collector cut off current | $V_{CE}=50V$ , $V_{BE}=0V$                 | _     | _    | 0.5   | μΑ     |
| $G_{I}$                         | DC forward current gain   | $V_{CE}$ =5 $V$ , $I_{C}$ =50 $mA$         | 47    | _    | _     | _      |
| $R_1$                           | Input resistor            | _  | 0.154 | 0.22 | 0.286 | kΩ     |
| R <sub>2</sub> /R <sub>1</sub>  | Resistor ratio            | -  | 17.1  | 21.3 | 25.6  | _      |
| $f_{\mathrm{T}}$                | Gain band width product   | $V_{CE}$ =10V, $I_{E}$ =-50mA, f=100MHz    | _     | 250  | _     | MHz    |

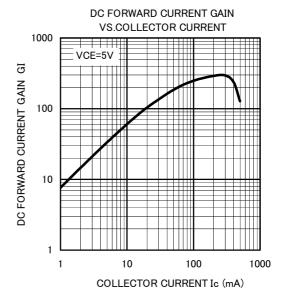
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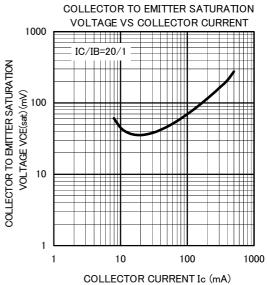
# TYPICAL CHARACTERISTICS(Ta=25°C)













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